Stacia Keller

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

244	6,918	42	73
papers	citations	h-index	g-index

253	7,810	3.1	5.67
ext. papers	ext. citations	avg, IF	L-index

#	Paper	IF	Citations
244	Demonstration of device-quality 60% relaxed In0.2Ga0.8N on porous GaN pseudo-substrates grown by PAMBE. *Journal of Applied Physics*, **2022**, 131, 015701	2.5	3
243	Acceptor traps as the source of holes in p-type N-polar GaN/(AlN/AlGaN) superlattices. *Applied Physics Letters*, **2022**, 120, 132104	3.4	2
242	Inverted N-polar blue and blue-green light emitting diodes with high power grown by metalorganic chemical vapor deposition. *Applied Physics Letters*, **2022**, 120, 101104	3.4	0
241	Demonstration of Acceptor-Like Traps at Positive Polarization Interfaces in Ga-Polar P-type (AlGaN/AlN)/GaN Superlattices. *Crystals*, **2022**, 12, 784	2.3	1
240	InGaN-Based microLED Devices Approaching 1% EQE with Red 609 nm Electroluminescence on Semi-Relaxed Substrates. *Crystals*, **2021**, 11, 1364	2.3	5
239	Properties of AlN/GaN Heterostructures Grown at Low Growth Temperatures with Ammonia and Dimethylhydrazine. *Crystals*, **2021**, 11, 1412	2.3	2
238	Demonstration of ultra-small (0.2%) for mini-displays. *Applied Physics Express*, **2021**, 14, 011004	2.4	35
237	MOCVD growth of thick V-pit-free InGaN films on semi-relaxed InGaN substrates. *Semiconductor Science and Technology*, **2021**, 36, 015011	1.8	4
236	2DEGs formed in AlN/GaN HEMT structures with AlN grown at low temperature. *Applied Physics Letters*, **2021**, 118, 222103	3.4	3
235	Metal Organic Vapor Phase Epitaxy of Thick N-Polar InGaN Films. *Electronics (Switzerland)*, **2021**, 10, 1182	2.6	3
234	Growth by MOCVD and photoluminescence of semipolar (202̄1̄) InN quantum dashes. *Journal of Crystal Growth*, **2021**, 563, 126093	1.6	2
233	6.2 W/Mm and Record 33.8% PAE at 94 GHz From N-Polar GaN Deep Recess MIS-HEMTs With ALD Ru Gates. *IEEE Microwave and Wireless Components Letters*, **2021**, 31, 748-751	2.6	13
232	Investigation and optimization of N-polar GaN porosification for regrowth of smooth hillocks-free GaN films. *Applied Physics Letters*, **2021**, 119, 042105	3.4	1
231	pH-Dependent surface charge at the interfaces between aluminum gallium nitride (AlGaN) and aqueous solution revealed by surfactant adsorption. *Journal of Colloid and Interface Science*, **2021**, 583, 331-339	9.3	1
230	Metalorganic chemical vapor deposition of InN quantum dots and nanostructures. *Light: Science and Applications*, **2021**, 10, 150	16.7	0
229	Evaluation of linearity at 30 GHz for N-polar GaN deep recess transistors with 10.3 W/mm of output power and 47.4% PAE. *Applied Physics Letters*, **2021**, 119, 072105	3.4	3
228	Realization of III-Nitride c-Plane microLEDs Emitting from 470 to 645 nm on Semi-Relaxed Substrates Enabled by V-Defect-Free Base Layers. *Crystals*, **2021**, 11, 1168	2.3	3

227	Effects of surface oxidation on the pH-dependent surface charge of oxidized aluminum gallium nitride. *Journal of Colloid and Interface Science*, **2021**, 603, 604-614	9.3	1
226	Quantitative investigation of indium distribution in InN wetting layers and dots grown by metalorganic chemical vapor deposition. *Applied Physics Express*, **2020**, 13, 065005	2.4	3
225	Improved operation stability of in situ AlSiO dielectric grown on (000) N-polar GaN by MOCVD. *Applied Physics Express*, **2020**, 13, 061010	2.4	5
224	Ultra-high silicon doped N-polar GaN contact layers grown by metal-organic chemical vapor deposition. *Semiconductor Science and Technology*, **2020**, 35, 095002	1.8	7
223	Flow modulation metalorganic vapor phase epitaxy of GaN at temperatures below 600 C. *Semiconductor Science and Technology*, **2020**, 35, 095014	1.8	5
222	Growth of strain-relaxed InGaN on micrometer-sized patterned compliant GaN pseudo-substrates. *Applied Physics Letters*, **2020**, 116, 111101	3.4	23
221	Bias-Dependent Electron Velocity Extracted From N-Polar GaN Deep Recess HEMTs. *IEEE Transactions on Electron Devices*, **2020**, 67, 1542-1546	2.9	6
220	High Linearity and High Gain Performance of N-Polar GaN MIS-HEMT at 30 GHz. *IEEE Electron Device Letters*, **2020**, 41, 681-684	4.4	17
219	Observation of ID-VD Kink in N-Polar GaN MIS-HEMTs at Cryogenic Temperatures. *IEEE Electron Device Letters*, **2020**, 41, 345-348	4.4	5
218	W-Band Power Performance of SiN-Passivated N-Polar GaN Deep Recess HEMTs. *IEEE Electron Device Letters*, **2020**, 41, 349-352	4.4	42
217	An improved methodology for extracting interface state density at Si3N4/GaN. *Applied Physics Letters*, **2020**, 116, 022104	3.4	13
216	First experimental demonstration and analysis of electrical transport characteristics of a GaN-based HEMT with a relaxed InGaN channel. *Semiconductor Science and Technology*, **2020**, 35, 075007	1.8	8
215	Interfacial N Vacancies in GaN/(Al,Ga)N/GaN Heterostructures. *Physical Review Applied*, **2020**, 13,	4.3	12
214	High-electron-mobility transistors with metal-organic chemical vapor deposition-regrown contacts for high voltage applications. *Semiconductor Science and Technology*, **2020**, 35, 124004	1.8	2
213	Compliant Micron-Sized Patterned InGaN Pseudo-Substrates Utilizing Porous GaN. *Materials*, **2020**, 13,	3.5	15
212	Characterization of AlSiO dielectrics with varying silicon composition for N-polar GaN-based devices. *Semiconductor Science and Technology*, **2020**, 35, 095027	1.8	7
211	Demonstration of a GaN/AlGaN Superlattice-Based p-Channel FinFET With High ON-Current. *IEEE Electron Device Letters*, **2020**, 41, 220-223	4.4	27
210	Optimization of Digital Growth of Thick N-Polar InGaN by MOCVD. *Journal of Electronic Materials*, **2020**, 49, 3450-3454	1.9	2

209	Growth of high-quality N-polar GaN on bulk GaN by plasma-assisted molecular beam epitaxy. *Solid State Communications*, **2020**, 305, 113763	1.6	5
208	AlGaN/GaN Superlattice-Based p-Type Field-Effect Transistor with Tetramethylammonium Hydroxide Treatment. *Physica Status Solidi (A) Applications and Materials Science*, **2020**, 217, 1900692	1.6	13
207	A Novel Concept using Derivative Superposition at the Device-Level to Reduce Linearity Sensitivity to Bias in N-polar GaN MISHEMT **2020**,		2
206	. *IEEE Electron Device Letters*, **2020**, 41, 1468-1471	4.4	3
205	Proposed existence of acceptor-like traps at positive polarization interfaces in p-type III-nitride semiconductors. *Applied Physics Letters*, **2020**, 117, 042104	3.4	8
204	Color-tunable . *Applied Physics Letters*, **2020**, 117, 061105	3.4	19
203	Method of growing elastically relaxed crack-free AlGaN on GaN as substrates for ultra-wide bandgap devices using porous GaN. *Applied Physics Letters*, **2020**, 117, 062102	3.4	8
202	N-Polar GaN-on-Sapphire Deep Recess HEMTs With High W-Band Power Density. *IEEE Electron Device Letters*, **2020**, 41, 1633-1636	4.4	12
201	A systematic and quantitative analysis of the bulk and interfacial properties of the AlSiO dielectric on N-polar GaN using capacitance�voltage methods. *Journal of Applied Physics*, **2020**, 128, 074101	2.5	3
200	MOCVD Growth and Characterization of InN Quantum Dots. *Physica Status Solidi (B): Basic Research*, **2020**, 257, 1900508	1.3	5
199	Fabrication of relaxed InGaN pseudo-substrates composed of micron-sized pattern arrays with high fill factors using porous GaN. *Semiconductor Science and Technology*, **2019**, 34, 115020	1.8	20
198	Characterization of InGaN quantum dots grown by metalorganic chemical vapor deposition. *Semiconductor Science and Technology*, **2019**, 34, 125002	1.8	4
197	Infrared luminescence from N-polar InN quantum dots and thin films grown by metal organic chemical vapor deposition. *Applied Physics Letters*, **2019**, 114, 241103	3.4	12
196	First demonstration of improvement in hole conductivity inc-plane III-Nitrides through application of uniaxial strain. *Japanese Journal of Applied Physics*, **2019**, 58, 030908	1.4	12
195	A Demonstration of Nitrogen Polar Gallium Nitride Current Aperture Vertical Electron Transistor. *IEEE Electron Device Letters*, **2019**, 40, 885-888	4.4	12
194	Properties of N-polar InGaN/GaN quantum wells grown with triethyl gallium and triethyl indium as precursors. *Semiconductor Science and Technology*, **2019**, 34, 075017	1.8	8
193	Electron transport in N-polar GaN-based heterostructures. *Applied Physics Letters*, **2019**, 114, 162102	3.4	8
192	Role of GaN cap layer for reference electrode free AlGaN/GaN-based pH sensors. *Sensors and Actuators B: Chemical*, **2019**, 287, 250-257	8.5	13

(2018-2019)

191	Net negative fixed interface charge for Si3N4 and SiO2 grown in situ on 000-1 N-polar GaN. *Applied Physics Letters*, **2019**, 115, 032103	3.4	11
190	Investigation of nitrogen polar p-type doped GaN/AlxGa(1-x)N superlattices for applications in wide-bandgap p-type field effect transistors. *Applied Physics Letters*, **2019**, 115, 172105	3.4	15
189	Electrical properties and interface abruptness of AlSiO gate dielectric grown on 000 1 N-polar and (0001) Ga-polar GaN. *Applied Physics Letters*, **2019**, 115, 172104	3.4	7
188	pH-dependent surface properties of the gallium nitride - Solution interface mapped by surfactant adsorption. *Journal of Colloid and Interface Science*, **2019**, 556, 680-688	9.3	3
187	Flatband voltage stability and time to failure of MOCVD-grown SiO2 and Si3N4 dielectrics on N-polar GaN. *Applied Physics Express*, **2019**, 12, 121001	2.4	4
186	First demonstration of RF N-polar GaN MIS-HEMTs grown on bulk GaN using PAMBE. *Semiconductor Science and Technology*, **2019**, 34, 045009	1.8	12
185	Virtual-Source Modeling of N-polar GaN MISHEMTS **2019**,		1
184	Enhanced mobility in vertically scaled N-polar high-electron-mobility transistors using GaN/InGaN composite channels. *Applied Physics Letters*, **2018**, 112, 073501	3.4	5
183	Analysis of MOCVD SiNx Passivated N-Polar GaN MIS-HEMTs on Sapphire With High $f_{max}cdot V_{DS,Q}$. *IEEE Electron Device Letters*, **2018**, 39, 409-412	4.4	13
182	Demonstration of GaN Current Aperture Vertical Electron Transistors With Aperture Region Formed by Ion Implantation. *IEEE Transactions on Electron Devices*, **2018**, 65, 483-487	2.9	27
181	Metal-organic chemical vapor deposition of N-polar InN quantum dots and thin films on vicinal GaN. *Journal of Applied Physics*, **2018**, 123, 055702	2.5	13
180	Demonstration of Constant 8 W/mm Power Density at 10, 30, and 94 GHz in State-of-the-Art Millimeter-Wave N-Polar GaN MISHEMTs. *IEEE Transactions on Electron Devices*, **2018**, 65, 45-50	2.9	98
179	Corrections to In Situ Oxide, GaN Interlayer-Based Vertical Trench MOSFET (OG-FET) on Bulk GaN Substrates[Mar 17 353-355]. *IEEE Electron Device Letters*, **2018**, 39, 316-316	4.4	3
178	880 V/ $2.7~text{m}Omegacdottext{cm}^{text{2}}$ MIS Gate Trench CAVET on Bulk GaN Substrates. *IEEE Electron Device Letters*, **2018**, 39, 863-865	4.4	54
177	Large-Area In-Situ Oxide, GaN Interlayer-Based Vertical Trench MOSFET (OG-FET). *IEEE Electron Device Letters*, **2018**, 39, 711-714	4.4	33
176	Investigation of Mg doping for low resistance N-polar p-GaN films grown at reduced temperatures by MOCVD. *Semiconductor Science and Technology*, **2018**, 33, 095014	1.8	9
175	Observation of Hot Electron and Impact Ionization in N-Polar GaN MIS-HEMTs. *IEEE Electron Device Letters*, **2018**, 39, 1007-1010	4.4	12
174	Improved Dynamic RON of GaN Vertical Trench MOSFETs (OG-FETs) Using TMAH Wet Etch. *IEEE Electron Device Letters*, **2018**, 39, 1030-1033	4.4	16

173	Growth of N-polar GaN by ammonia molecular beam epitaxy. *Journal of Crystal Growth*, **2018**, 481, 65-70	1.6	8
172	N-Polar GaN HEMTs Exhibiting Record Breakdown Voltage Over 2000 V and Low Dynamic On-Resistance. *IEEE Electron Device Letters*, **2018**, 39, 1014-1017	4.4	50
171	N-Polar GaN Cap MISHEMT With Record Power Density Exceeding 6.5 W/mm at 94 GHz. *IEEE Electron Device Letters*, **2017**, 38, 359-362	4.4	56
170	Suppression of Mg propagation into subsequent layers grown by MOCVD. *Journal of Applied Physics* , **2017**, 121, 025106	2.5	20
169	Exploring metalorganic chemical vapor deposition of Si-alloyed Al 2 O 3 dielectrics using disilane. *Journal of Crystal Growth*, **2017**, 464, 54-58	1.6	6
168	Compositionally graded InGaN layers grown on vicinal N-face GaN substrates by plasma-assisted molecular beam epitaxy. *Journal of Crystal Growth*, **2017**, 465, 55-59	1.6	12
167	In Situ Oxide, GaN Interlayer-Based Vertical Trench MOSFET (OG-FET) on Bulk GaN substrates. *IEEE Electron Device Letters*, **2017**, 38, 353-355	4.4	99
166	Indium segregation in N-polar InGaN quantum wells evidenced by energy dispersive X-ray spectroscopy and atom probe tomography. *Applied Physics Letters*, **2017**, 110, 143101	3.4	29
165	Metal-organic chemical vapor deposition of high quality, high indium composition N-polar InGaN layers for tunnel devices. *Journal of Applied Physics*, **2017**, 121, 185707	2.5	16
164	Vertical transport in isotype InAlN/GaN dipole induced diodes grown by molecular beam epitaxy. *Journal of Applied Physics*, **2017**, 121, 205702	2.5	2
163	Dispersion Free 450-V p GaN-Gated CAVETs With Mg-ion Implanted Blocking Layer. *IEEE Electron Device Letters*, **2017**, 38, 933-936	4.4	35
162	Normally OFF Trench CAVET With Active Mg-Doped GaN as Current Blocking Layer. *IEEE Transactions on Electron Devices*, **2017**, 64, 805-808	2.9	58
161	Abrupt GaN/p-GaN:Mg junctions grown via metalorganic chemical vapor deposition. *Applied Physics Express*, **2017**, 10, 111002	2.4	5
160	P� junction diodes with polarization induced p-type graded InxGa1�N layer. *Semiconductor Science and Technology*, **2017**, 32, 105013	1.8	7
159	Impact of Trench Dimensions on the Device Performance of GaN Vertical Trench MOSFETs. *IEEE Electron Device Letters*, **2017**, 38, 1559-1562	4.4	6
158	Characterization of N-polar AlN in GaN/AlN/(Al,Ga)N heterostructures grown by metal-organic chemical vapor deposition. *Semiconductor Science and Technology*, **2017**, 32, 115004	1.8	5
157	Atom Probe Tomography Quantification of Alloy Fluctuations in (Al,In,Ga)N. *Microscopy and Microanalysis*, **2017**, 23, 716-717	0.5	1
156	Maskless regrowth of GaN for trenched devices by MOCVD. *Applied Physics Letters*, **2017**, 111, 233507	3.4	3

155	Impact of oxygen precursor flow on the forward bias behavior of MOCVD-Al2O3 dielectrics grown on GaN. *Journal of Applied Physics*, **2017**, 122, 174101	2.5	3
154	Growth of high purity N-polar (In,Ga)N films. *Journal of Crystal Growth*, **2017**, 464, 127-131	1.6	21
153	. *IEEE Electron Device Letters*, **2017**, 38, 1575-1578	4.4	25
152	High Spatial Resolution Energy Dispersive X-ray Spectroscopy and Atom Probe Tomography study of Indium segregation in N-polar InGaN Quantum Wells. *Microscopy and Microanalysis*, **2017**, 23, 1448-1449	0.5	1
151	Digital growth of thick N-polar InGaN films on relaxed InGaN pseudosubstrates. *Applied Physics Express*, **2017**, 10, 111001	2.4	11
150	Demonstrating >1.4 kV OG-FET performance with a novel double field-plated geometry and the successful scaling of large-area devices **2017**,		39
149	Comparing electrical performance of GaN trench-gate MOSFETs witha-plane $(11bar{2}0)$ andm-plane $(1bar{1}00)$ sidewall channels. *Applied Physics Express*, **2016**, 9, 121001	2.4	38
148	High frequency N-polar GaN planar MIS-HEMTs on sapphire with high breakdown and low dispersion **2016**,		10
147	N-Polar GaN MIS-HEMTs on Sapphire With High Combination of Power Gain Cutoff Frequency and Three-Terminal Breakdown Voltage. *IEEE Electron Device Letters*, **2016**, 37, 77-80	4.4	27
146	Plasma-assisted molecular beam epitaxy growth diagram of InGaN on (0001)GaN for the optimized synthesis of InGaN compositional grades. *Physica Status Solidi (B): Basic Research*, **2016**, 253, 626-629	1.3	11
145	Plasma-assisted molecular beam epitaxy growth diagram of InGaN on (0001)GaN for the optimized synthesis of InGaN compositional grades (Phys. Status Solidi B 4/2016). *Physica Status Solidi (B): Basic Research*, **2016**, 253, 792-792	1.3	
144	Performance projection of III-nitride heterojunction nanowire tunneling field-effect transistors. *Physica Status Solidi (A) Applications and Materials Science*, **2016**, 213, 905-908	1.6	10
143	Controlled low Si doping and high breakdown voltages in GaN on sapphire grown by MOCVD. *Semiconductor Science and Technology*, **2016**, 31, 125018	1.8	13
142	Optimization of a chlorine-based deep vertical etch of GaN demonstrating low damage and low roughness. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2016**, 34, 031303	2.9	11
141	Polarity in GaN and ZnO: Theory, measurement, growth, and devices. *Applied Physics Reviews*, **2016**, 3, 041303	17.3	85
140	Model to explain the behavior of 2DEG mobility with respect to charge density in N-polar and Ga-polar AlGaN-GaN heterostructures. *Journal of Applied Physics*, **2016**, 120, 115302	2.5	26
139	N-Polar Deep Recess MISHEMTs With Record 2.9 W/mm at 94 GHz. *IEEE Electron Device Letters*, **2016**, 1-1	4.4	18
138	OG-FET: An In-Situ ${O}$ xide, ${G}$ aN Interlayer-Based Vertical Trench MOSFET. *IEEE Electron Device Letters*, **2016**, 37, 1601-1604	4.4	49

137	Design Space of III-N Hot Electron Transistors Using AlGaN and InGaN Polarization-Dipole Barriers. *IEEE Electron Device Letters*, **2015**, 36, 23-25	4.4	4
136	Unintentional gallium incorporation in AlN and its impact on the electrical properties of GaN/AlN and GaN/AlN/AlGaN heterostructures. *Semiconductor Science and Technology*, **2015**, 30, 055015	1.8	11
135	Method to Predict and Optimize Charge Sensitivity of Ungated AlGaN/GaN HEMT-Based Ion Sensor Without Use of Reference Electrode. *IEEE Sensors Journal*, **2015**, 15, 5320-5326	4	9
134	Relaxedc-plane InGaN layers for the growth of strain-reduced InGaN quantum wells. *Semiconductor Science and Technology*, **2015**, 30, 105015	1.8	34
133	InGaN lattice constant engineering via growth on (In,Ga)N/GaN nanostripe arrays. *Semiconductor Science and Technology*, **2015**, 30, 105020	1.8	10
132	Measuring the signature of bias and temperature-dependent barrier heights in III-N materials using a hot electron transistor. *Semiconductor Science and Technology*, **2015**, 30, 105003	1.8	2
131	Barrier height fluctuations in InGaN polarization dipole diodes. *Applied Physics Letters*, **2015**, 107, 173503	3.4	4
130	Design, fabrication, and performance analysis of GaN vertical electron transistors with a buried p/n junction. *Applied Physics Letters*, **2015**, 106, 183502	3.4	68
129	Common emitter operation of III-N HETs using AlGaN and InGaN polarization-dipole induced barriers **2014**,		1
128	Elimination of columnar microstructure in N-face InAlN, lattice-matched to GaN, grown by plasma-assisted molecular beam epitaxy in the N-rich regime. *Applied Physics Letters*, **2014**, 104, 072107	3.4	18
127	Improved properties of high-Al-composition AlGaN/GaN high electron mobility transistor structures with thin GaN cap layers. *Japanese Journal of Applied Physics*, **2014**, 53, 095504	1.4	7
126	Design of polarization-dipole-induced isotype heterojunction diodes for use in IIIN hot electron transistors. *Applied Physics Express*, **2014**, 7, 014102	2.4	10
125	Low ON-resistance and high current GaN Vertical Electron Transistors with buried p-GaN layers **2014**,		4
124	Engineering the (In, Al, Ga)N back-barrier to achieve high channel-conductivity for extremely scaled channel-thicknesses in N-polar GaN high-electron-mobility-transistors. *Applied Physics Letters*, **2014**, 104, 092107	3.4	18
123	Measurement of the hot electron mean free path and the momentum relaxation rate in GaN. *Applied Physics Letters*, **2014**, 105, 263506	3.4	23
122	Recent progress in metal-organic chemical vapor deposition of $left(000bar{1} right)$ N-polar group-III nitrides. *Semiconductor Science and Technology*, **2014**, 29, 113001	1.8	129
121	Dielectric stress tests and capacitance-voltage analysis to evaluate the effect of post deposition annealing on Al2O3 films deposited on GaN. *Applied Physics Letters*, **2014**, 105, 222905	3.4	10
120	Extraction of net interfacial polarization charge from Al0.54In0.12Ga0.34N/GaN high electron mobility transistors grown by metalorganic chemical vapor deposition. *Journal of Applied Physics*, **2014**, 116, 183704	2.5	4

119	A donor-like trap at the InGaN/GaN interface with net negative polarization and its possible consequence on internal quantum efficiency. *Semiconductor Science and Technology*, **2013**, 28, 105021	1.8	9
118	Capacitance-voltage characterization of interfaces between positive valence band offset dielectrics and wide bandgap semiconductors. *Journal of Applied Physics*, **2013**, 114, 083718	2.5	34
117	Atom probe analysis of AlN interlayers in AlGaN/AlN/GaN heterostructures. *Applied Physics Letters*, **2013**, 102, 111603	3.4	55
116	N-polar GaN epitaxy and high electron mobility transistors. *Semiconductor Science and Technology*, **2013**, 28, 074009	1.8	124
115	Development of gallium-nitride-based light-emitting diodes (LEDs) and laser diodes for energy-efficient lighting and displays. *Acta Materialia*, **2013**, 61, 945-951	8.4	283
114	Very high channel conductivity in ultra-thin channel N-polar GaN/(AlN, InAlN, AlGaN) high electron mobility hetero-junctions grown by metalorganic chemical vapor deposition. *Applied Physics Letters*, **2013**, 102, 232104	3.4	19
113	Impact of Moisture and Fluorocarbon Passivation on the Current Collapse of AlGaN/GaN HEMTs. *IEEE Electron Device Letters*, **2012**, 33, 1378-1380	4.4	29
112	Microwave Power Performance N-Polar GaN MISHEMTs Grown by MOCVD on SiC Substrates Using an $hbox{Al}_{2}hbox{O}_{3}$ Etch-Stop Technology. *IEEE Electron Device Letters*, **2012**, 33, 44-46	4.4	30
111	Design of High-Aspect-Ratio T-Gates on N-Polar GaN/AlGaN MIS-HEMTs for High f_{max}. *IEEE Electron Device Letters*, **2012**, 33, 785-787	4.4	40
110	Effect of indium on the conductivity of poly-crystalline GaN grown on high purity fused silica. *Physica Status Solidi (A) Applications and Materials Science*, **2012**, 209, 431-433	1.6	3
109	Enhancement-mode m -plane AlGaN/GaN HFETs with regrown n+-GaN contact layer. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 891-893		3
108	InGaAs-InGaN Wafer-Bonded Current Aperture Vertical Electron Transistors (BAVETs). *Journal of Electronic Materials*, **2012**, 41, 857-864	1.9	6
107	Effect of quantum well cap layer thickness on the microstructure and performance of InGaN/GaN solar cells. *Applied Physics Letters*, **2012**, 100, 161101	3.4	47
106	Charge and Mobility Enhancements in In-Polar InAl(Ga)N/Al(Ga)N/GaN Heterojunctions Grown by MetalOrganic Chemical Vapor Deposition Using a Graded Growth Strategy. *Japanese Journal of Applied Physics*, **2012**, 51, 115502	1.4	6
105	Charge and Mobility Enhancements in In-Polar InAl(Ga)N/Al(Ga)N/GaN Heterojunctions Grown by MetalOrganic Chemical Vapor Deposition Using a Graded Growth Strategy. *Japanese Journal of Applied Physics*, **2012**, 51, 115502	1.4	3
104	High internal and external quantum efficiency InGaN/GaN solar cells. *Applied Physics Letters*, **2011**, 98, 021102	3.4	155
103	Self-Aligned Technology for N-Polar GaN/Al(Ga)N MIS-HEMTs. *IEEE Electron Device Letters*, **2011**, 32, 33-35	4.4	14
102	N-Polar GaN/AlN MIS-HEMT With $f_{rm MAX}$ of 204 GHz for Ka-Band Applications. *IEEE Electron Device Letters*, **2011**, 32, 1683-1685	4.4	15

101	. *IEEE Transactions on Electron Devices*, **2011**, 58, 2589-2596	2.9	17
100	Two-Stage High-Gain High-Power Distributed Amplifier Using Dual-Gate GaN HEMTs. *IEEE Transactions on Microwave Theory and Techniques*, **2011**, 59, 2059-2063	4.1	28
99	Growth study and impurity characterization of AlxIn1□N grown by metal organic chemical vapor deposition. *Journal of Crystal Growth*, **2011**, 324, 163-167	1.6	45
98	Growth and characterization of N-polar GaN and AlGaN/GaN HEMTs on (111) silicon. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2086-2088		5
97	Enhancement-Mode m-plane AlGaN/GaN Heterojunction Field-Effect Transistors with +3 V of Threshold Voltage Using Al_2O_3 Deposited by Atomic Layer Deposition. *Applied Physics Express*, **2011**, 4, 096501	2.4	17
96	Effect of doping and polarization on carrier collection in InGaN quantum well solar cells. *Applied Physics Letters*, **2011**, 98, 243507	3.4	55
95	N-Polar GaN MIS-HEMTs With a 12.1-W/mm Continuous-Wave Output Power Density at 4 GHz on Sapphire Substrate. *IEEE Electron Device Letters*, **2011**, 32, 635-637	4.4	26
94	RF Performance of Deep-Recessed N-Polar GaN MIS-HEMTs Using a Selective Etch Technology Without Ex Situ Surface Passivation. *IEEE Electron Device Letters*, **2011**, 32, 134-136	4.4	10
93	Observation of positive thermal power coefficient in InGaN/GaN quantum well solar cells. *Applied Physics Letters*, **2011**, 99, 071104	3.4	16
92	Temperature Dependent Capacitance□Voltage Analysis of Unintentionally Doped and Si Doped $Al_{0.82}In_{0.18}N$ Grown on GaN. *Japanese Journal of Applied Physics*, **2011**, 50, 101001	1.4	1
91	N-polar GaN-based MIS-HEMTs for mixed signal applications **2010**,		1
90	Growth and characterization of In-polar and N-polar InAlN by metal organic chemical vapor deposition. *Journal of Applied Physics*, **2010**, 107, 033509	2.5	26
89	Low Ohmic Contact Resistancem-Plane AlGaN/GaN Heterojunction Field-Effect Transistors with Enhancement-Mode Operations. *Applied Physics Express*, **2010**, 3, 101002	2.4	12
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